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July 2007

FDI8441

N-Channel PowerTrench® MOSFET 40V, 80A, 2.7m Ω

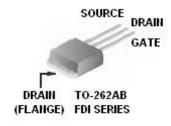
Features

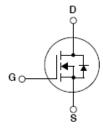
- Typ $r_{DS(on)}$ = 2.2m Ω at V_{GS} = 10V, I_D = 80A
- Typ $Q_{g(10)}$ = 215nC at V_{GS} = 10V
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- RoHS Compliant

Applications

- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Steering
- Integrated Starter / Alternator
- Distributed Power Architectures and VRMs
- Primary Switch for 12V Systems







MOSFET Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		40	V
V_{GS}	Gate to Source Voltage		±20	V
	Drain Current Continuous (T _C < 160°C, V _{GS} = 10V)		80	
I_D	Continuous ($T_{amb} = 25^{\circ}C$, $V_{GS} = 10V$, with $R_{\theta JA} = 43^{\circ}C/W$)		26	Α
	Pulsed		See Figure 4	
E _{AS}	Single Pulse Avalanche Energy (I	Note 1)	947	mJ
D	Power dissipation		300	W
P_{D}	Derate above 25°C		2	W/°C
T _J , T _{STG}	Operating and Storage Temperature		-55 to 175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case		0.5	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	(Note 2)	62	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, 1in ² copper pad area		43	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDI8441	FDI8441	TO-262AB	Tube	NA	50 units

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units

Off Characteristics

B _{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250 \text{mA}, V_C$	_{SS} = 0V	40	-	-	V
	Zero Gate Voltage Drain Current	$V_{DS} = 32V$		-	-	1	
IDSS	Zero Gate Voltage Drain Current	$V_{GS} = 0V$	$T_J = 150$ °C	-	-	250	μΑ
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V$	·	-	-	±100	nA

On Characteristics

V_{G}	SS(th)	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	2.8	4	V
			I _D = 80A, V _{GS} = 10V	-	2.2	2.7	
r _{DS}	S(on)	Drain to Source On Resistance	I _D = 80A, V _{GS} = 10V, T _J = 175°C	-	3.8	4.7	mΩ

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05V V 0V		-	15000	-	pF
C _{oss}	Output Capacitance	f = 1MHz	$V_{DS} = 25V, V_{GS} = 0V,$		1250	-	pF
C _{rss}	Reverse Transfer Capacitance	1 - 11011 12		-	685	-	pF
R_G	Gate Resistance	V _{GS} = 0.5V, f = 1MHz		-	1.1	-	Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V		-	215	280	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to $2V$	V _{DD} = 20V	-	29	38	nC
Q_{gs}	Gate to Source Gate Charge		$I_{D} = 35A$	-	60	-	nC
Q _{gs2}	Gate Charge Threshold to Plateau		$I_g = 1mA$	-	32	-	nC
Q_{gd}	Gate to Drain "Miller" Charge			-	49	ı	nC

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbol Parameter Test Condition	s Min Typ	Max Units
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Switching Characteristics

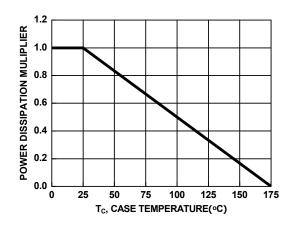
t _(on)	Turn-On Time		-	-	77	ns
t _{d(on)}	Turn-On Delay Time		-	23	-	ns
t _r	Turn-On Rise Time	V _{DD} = 20V, I _D = 35A	-	24	-	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10V, R_{GS} = 1.5 Ω	-	75	-	ns
t _f	Turn-Off Fall Time		-	17.9	-	ns
t _{off}	Turn-Off Time		-	-	147	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	I _{SD} = 35A	-	0.8	1.25	V
	Source to Drain Diode voltage	I _{SD} = 15A	-	0.8	1.0	V
t _{rr}	Reverse Recovery Time	I _F = 35A, di/dt = 100A/μs	-	52	68	ns
Q _{rr}	Reverse Recovery Charge	I _F = 35A, di/dt = 100A/μs	-	76	99	nC

Notes: 1: Starting $T_J = 25^{\circ}C$, L = 0.46mH, $I_{AS} = 64A$. 2: Pulse width = 100s.

Typical Characteristics



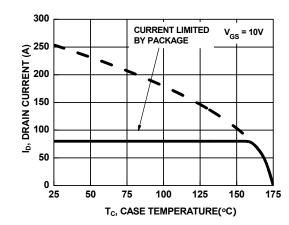


Figure 1. Normalized Power Dissipation vs Case Temperature

Figure 2. Maximum Continuous Drain Current vs Case Temperature

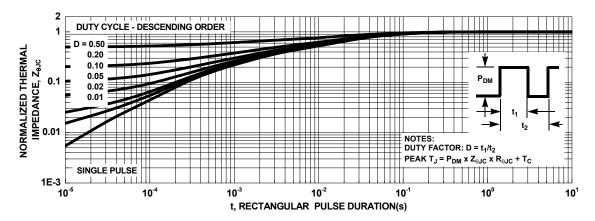


Figure 3. Normalized Maximum Transient Thermal Impedance

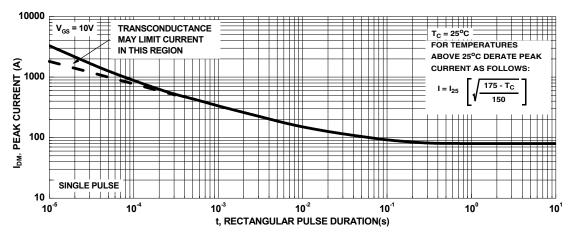


Figure 4. Peak Current Capability

Typical Characteristics

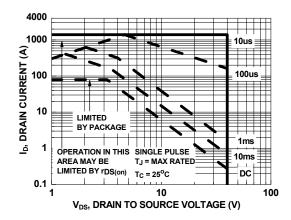
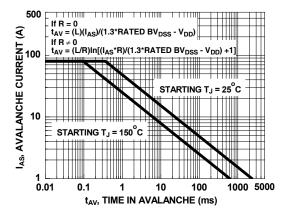


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching

Capability

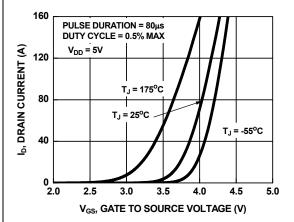


Figure 7. Transfer Characteristics

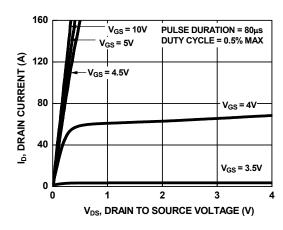


Figure 8. Saturation Characteristics

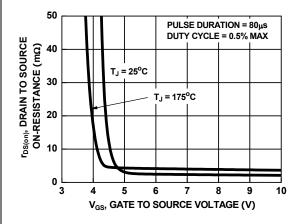


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

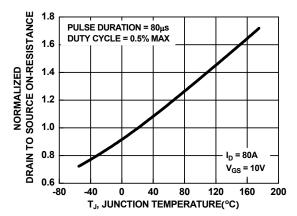


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics

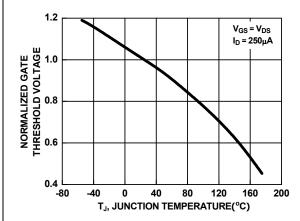


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

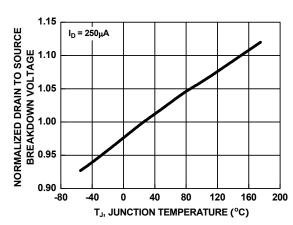


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

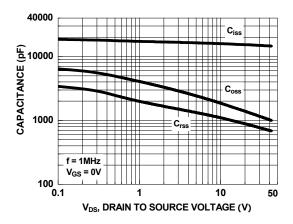


Figure 13. Capacitance vs Drain to Source Voltage

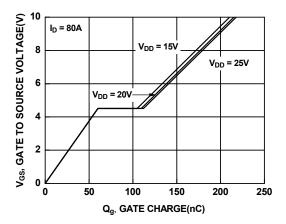


Figure 14. Gate Charge vs Gate to Source Voltage





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